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100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = 25°C
40014	3.0Ω @ $V_{GS} = 10V$	0.6A
100V	4.5Ω @ V _{GS} = 5.0V	0.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

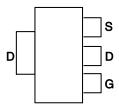
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.112 grams (Approximate)

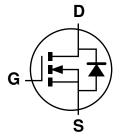




Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

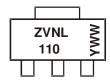
Part Number	Compliance	Case	Packaging
ZVNL110GTA	Standard	SOT223	1,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



ZVNL110 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	0.6 0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle ≦ 1%)			I _{DM}	6	Α
Maximum Body Diode Continuous Current (Note 6)			Is	1.5	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation	(Note 5)	Б	1.1	W
Total Power Dissipation	(Note 6)	P _D	2.0	
Thermal Desistance Junction to Ambient	(Note 5)	Б	113	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	61	
Thermal Resistance, Junction to Case	R _{θJC}	6.6		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

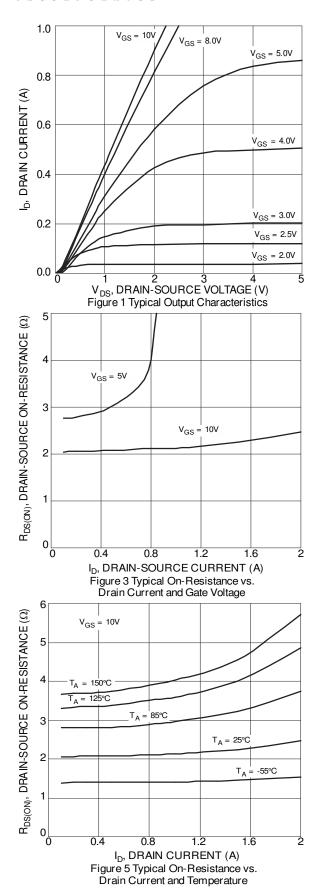
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

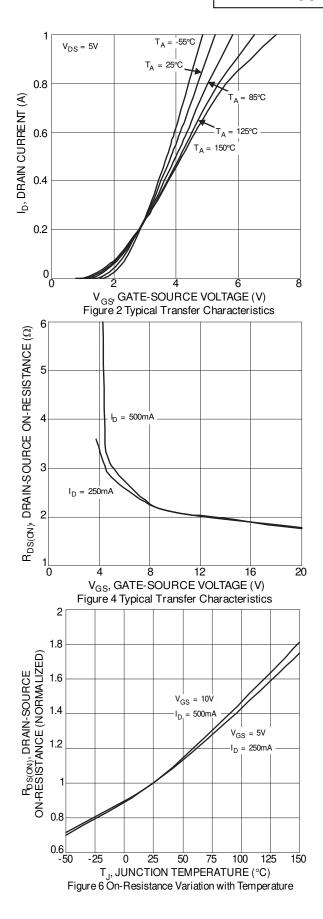
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}			10 100	μΑ	$V_{DS} = 100V, V_{GS} = 0V$ $V_{DS} = 80V, V_{GS} = 0V, T_{J} = +125$ °C	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current	I _{D(ON)}	750	_	_	mA	$V_{DS} = 25V, V_{GS} = 5V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.75		1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}			3.0	Ω	$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-nesistance		_	_	4.5		$V_{GS} = 5.0V, I_D = 250mA$	
Forward Transconductance	g _{fs}	225	_	_	mS	V _{DS} = 25V, I _D = 500mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		47	75		$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Output Capacitance	Coss		23	25	pF		
Reverse Transfer Capacitance	C _{rss}	_	6	8			
Turn-On Delay Time	t _{D(ON)}	_	2	7		$V_{DD} = 25V, V_{GS} = 10V,$ $R_G = 6.0\Omega, I_D = 1.0A$	
Turn-On Rise Time	t _R	_	3	12			
Turn-Off Delay Time	t _{D(OFF)}	_	5	15	ns		
Turn-Off Fall Time	t _F	_	2	13			

Notes:

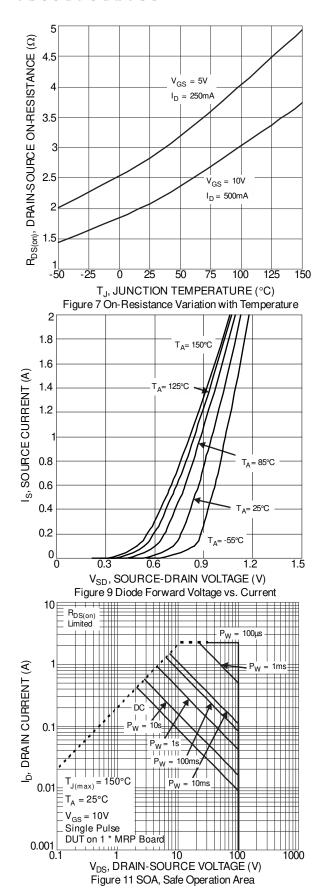
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

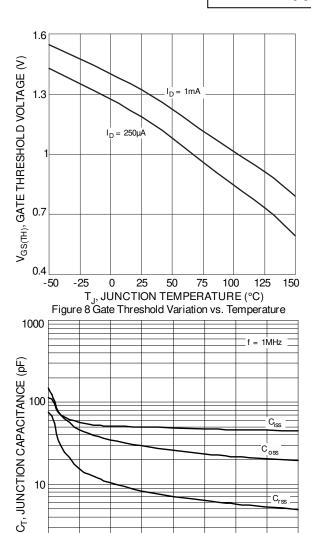












15

20

V_{DS}, DRAIN-SOURCE VOLTAGE (V)

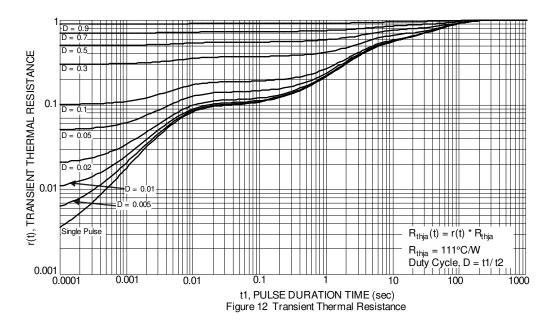
Figure 10 Typical Junction Capacitance

25

1

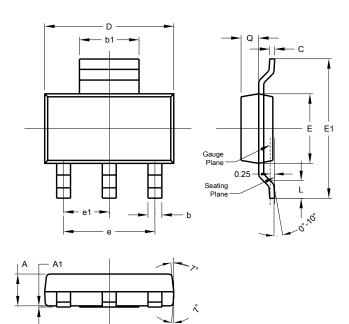
C_{rss}





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

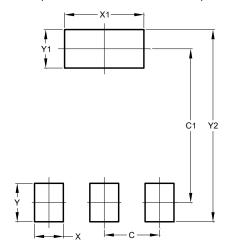


SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A 1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
C	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	1	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	2.30			
C1	6.40			
Х	1.20			
X1	3.30			
Υ	1.60			
Y1	1.60			
C2	8.00			

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